

2-input NOR Gate

REJ03D0183-0500Z (Previous ADE-205-310C (Z)) Rev.5.00 Jan.27.2004

# Description

The HD74HC1G02 is high speed CMOS two input NOR gate using silicon gate CMOS process. With CMOS low power dissipation, it provides high-speed equivalent to LS–TTL series. The internal circuit of three stages construction with buffer provides wide noise margin and stable output.

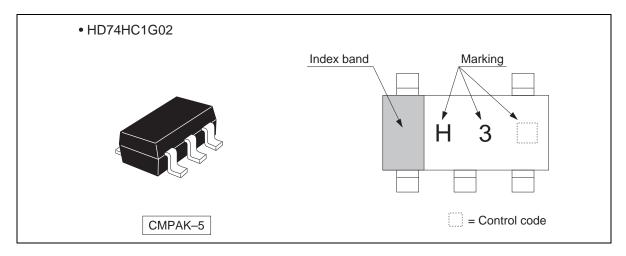
# Features

- The basic gate function is lined up as Renesas uni logic series.
- Supplied on emboss taping for high-speed automatic mounting.
- Electrical characteristics equivalent to the HD74HC02 Supply voltage range : 2 to 6 V Operating temperature range : -40 to +85°C
- $|I_{OH}| = I_{OL} = 2 \text{ mA (min)}$
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD74HC1G02CME	CMPAK-5 pin	CMPAK-5V	СМ	E (3,000 pcs/reel)



# **Outline and Article Indication**



# **Function Table**

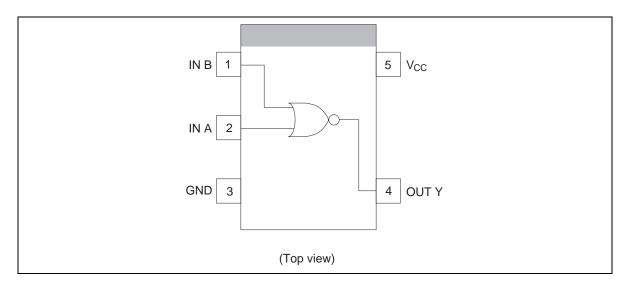
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Inputs			
A	В	Output Y	
L	L	н	
L	Н	L	
Н	L	L	
Н	Н	L	

H : High level

L : Low level

# **Pin Arrangement**





### **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit	Test Conditions		
Supply voltage range	V <sub>CC</sub>	–0.5 to 7.0	V			
Input voltage range *1	VI	–0.5 to V <sub>CC</sub> + 0.5	V			
Output voltage range *1, 2	Vo	-0.5 to V <sub>CC</sub> + 0.5	V	Output : H or L		
Input clamp current	I <sub>IK</sub>	±20	mA	$V_l < 0 \text{ or } V_l > V_{CC}$		
Output clamp current	Ι <sub>ΟK</sub>	±20	mA	$V_0 < 0$ or $V_0 > V_{CC}$		
Continuous output current	lo	±25	mA	$V_0 = 0$ to $V_{CC}$		
Continuous current through $V_{CC}$ or GND	I <sub>CC</sub> or I <sub>GND</sub>	±25	mA			
Maximum power dissipation at Ta = 25°C (in still air) $^{*3}$	P <sub>T</sub>	200	mW			
Storage temperature	Tstg	-65 to 150	°C			

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 2. This value is limited to 5.5 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

# **Recommended Operating Conditions**

Item	Symbol	Min	Max	Unit	<b>Test Conditions</b>
Supply voltage range	V <sub>CC</sub>	2	6	V	
Input voltage range	VI	0	V <sub>CC</sub>	V	
Output voltage range	Vo	0	V <sub>CC</sub>	V	
Output current	I <sub>OL</sub>		2.0	mA	$V_{CC} = 4.5 V$
		—	2.6		$V_{CC} = 6.0 V$
	I <sub>OH</sub>		-2.0	mA	$V_{CC} = 4.5 V$
		_	-2.6		$V_{CC} = 6.0 V$
Input rise / fall time	t <sub>r</sub> , t <sub>f</sub>	0	1000	ns	$V_{CC} = 2.0 V$
(10% to 90%)		0	500		$V_{CC} = 4.5 V$
		0	400		$V_{CC} = 6.0 V$
Operating temperature	Та	-40	85	°C	

Note: Unused or floating inputs must be held high or low.



# **Electrical Characteristics**

		$V_{CC} \qquad T_a = 25^{\circ}C \qquad \qquad T_a = -40 \text{ to } 85^{\circ}C$									
Item	Symbol	(V)	Min	Тур	Max	Min	Max	Unit	Test Conditions		
Input voltage	V <sub>IH</sub>	2.0	1.5			1.5	_	V			
		4.5	3.15	—	—	3.15	_	-			
		6.0	4.2	_		4.2		_			
	VIL	2.0		_	0.5	—	0.5	_			
		4.5	—	—	1.35	—	1.35	_			
		6.0	—		1.8	_	1.8	_			
Output voltage	V <sub>OH</sub>	2.0	1.9	2.0		1.9	_	V	V <sub>IN</sub> =	I <sub>OH</sub> = -20 μA	
		4.5	4.4	4.5		4.4	_	_	$V_{\text{IH}} \text{ or } V_{\text{IL}}$		
		6.0	5.9	6.0		5.9	_	_			
		4.5	4.18	4.31		4.13	_	_		$I_{OH} = -2 \text{ mA}$	
		6.0	5.68	5.80	_	5.63	_	_		$I_{OH} = -2.6 \text{ mA}$	
	V <sub>OL</sub>	2.0	—	0.0	0.1	—	0.1	_		$I_{OL} = 20 \ \mu A$	
		4.5	—	0.0	0.1	—	0.1	_			
		6.0		0.0	0.1	_	0.1	_			
		4.5	—	0.17	0.26	—	0.33	_		$I_{OL} = 2 \text{ mA}$	
		6.0	_	0.18	0.26	_	0.33	_		I <sub>OL</sub> = 2.6 mA	
Input current	l <sub>IN</sub>	6.0	_	_	±0.1	_	±1.0	μA	$V_{IN} = V_{CC} \text{ or } GND$		
Operating current	I <sub>CC</sub>	6.0	_	_	1.0	_	10.0	μΑ	$V_{\text{IN}} = V_{\text{CC}}$	or GND	



## **Switching Characteristics**

		Ta = 25	°C				
Item	Symbol	Min	Тур	Тур Мах		Test Conditions	
Output rise / fall time	t <sub>TLH</sub> t <sub>THL</sub>	_	5	10	ns	Test circuit	
Propagation delay time	t <sub>PLH</sub> t <sub>PHL</sub>	—	7	15	ns	Test circuit	

 $(C_L = 15 \text{ pF}, t_r = t_f = 6 \text{ ns}, V_{CC} = 5 \text{ V})$ 

		Vcc	Ta = 25°C		Ta = −40 to 85°C				
Item	Symbol	(V)	Min	Тур	Max	Min	Max	Unit	Test Conditions
Output rise / fall time	t <sub>TLH</sub>	2.0		50	125	—	155	ns	Test circuit
	t <sub>THL</sub>	4.5	—	14	25	_	31	-	
		6.0		12	21	_	26	-	
Propagation delay time	t <sub>PLH</sub>	2.0		48	100	_	125	ns	Test circuit
	t <sub>PHL</sub>	4.5		12	20	_	25	-	
		6.0	_	9	17	_	21	-	
Input capacitance	C <sub>IN</sub>	_		2.5	5	_	5	pF	
Equivalent capacitance	CPD	—		10	—	—	_	pF	

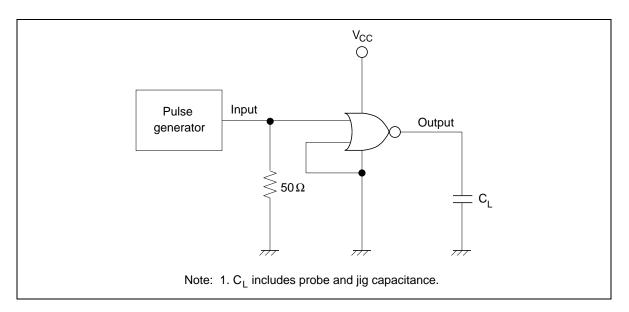
 $(C_L = 50 \text{ pF}, t_r = t_f = 6 \text{ ns})$ 

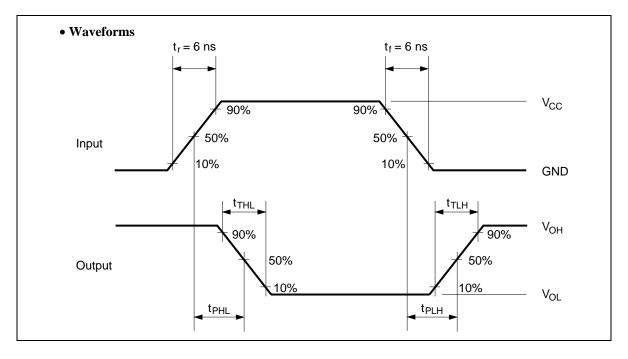
Note: C<sub>PD</sub> is equivalent capacitance inside of the IC calculated from the operating current without load (see test circuit). The average operating current without load is calculated according to the expression below.

 $I_{CC}$  (opr) =  $C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}$ 



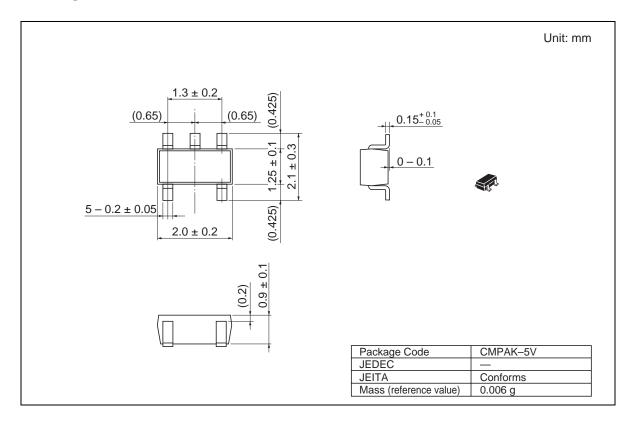
# **Test Circuit**







# **Package Dimensions**





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